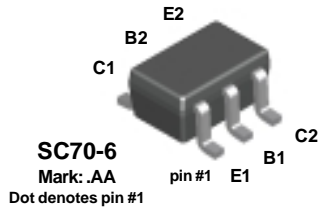
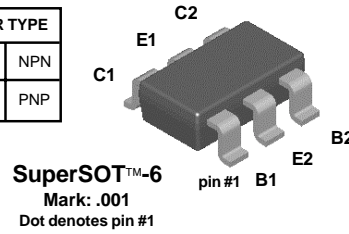


FFB2227A



TRANSISTOR TYPE			
C1	B1	E1	NPN
C2	B2	E2	PNP

FMB2227A



NPN & PNP General Purpose Amplifier

This complementary device is for use as a medium power amplifier and switch requiring collector currents up to 500 mA. Sourced from Process 19 and 63. See FFB2222A (NPN) and FFB2907A (PNP) for characteristics.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristic	Max		Units
		FFB2227A	FMB2227A	
P_D	Total Device Dissipation	300	700	mW
	Derate above 25°C	2.4	5.6	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	415	180	$^\circ\text{C}/\text{W}$

NPN & PNP General Purpose Amplifier

(continued)

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 10\text{ mA}, I_B = 0$	30			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\text{ }\mu\text{A}, I_E = 0$	60			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	5.0			V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 50\text{ V}, I_E = 0$			30	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 3.0\text{ V}, I_C = 0$			30	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 1.0\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 10\text{ mA}, V_{CE} = 10\text{ V}$ $I_C = 150\text{ mA}, V_{CE} = 10\text{ V}^*$ $I_C = 300\text{ mA}, V_{CE} = 10\text{ V}^*$	50 75 100 30			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$ $I_C = 300\text{ mA}, I_B = 30\text{ mA}$			0.4 1.4	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage*	$I_C = 150\text{ mA}, I_B = 15\text{ mA}$			1.3	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 50\text{ mA}, V_{CE} = 20\text{ V},$ $f = 100\text{ MHz}$		250		MHz
C_{obo}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 100\text{ kHz}$		4.0		pF
C_{ibo}	Input Capacitance	$V_{EB} = 2.0\text{ V}, I_C = 0, f = 100\text{ kHz}$		12		pF
NF	Noise Figure	$I_C = 100\text{ }\mu\text{A}, V_{CE} = 10\text{ V},$ $R_S = 1.0\text{ k}\Omega, f = 1.0\text{ kHz}$		2.0		dB

SWITCHING CHARACTERISTICS

t_{on}	Turn-on Time	$V_{CC} = 30\text{ V}, I_C = 150\text{ mA},$ $I_{B1} = 15\text{ mA}$		30		ns
t_d	Delay Time			8.0		ns
t_r	Rise Time			20		ns
t_{off}	Turn-off Time	$V_{CC} = 6.0\text{ V}, I_C = 150\text{ mA}$ $I_{B1} = I_{B2} = 15\text{ mA}$		80		ns
t_s	Storage Time			60		ns
t_f	Fall Time			20		ns

*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

FFB2227A / FMB2227A